

L Number	Hits	Search Text	DB	Time stamp
-	46	crystal\$4 or crystallin\$4 or epitax\$4 near10 silicon adj carbide or sic and 117/84-109.ccls. and partial near4 pressure	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 13:21
-	23	(silicon adj carbide or sic) near10 (CVD or chemical near2 vapor near2 deposit\$4 or ale or ald or atomic adj layer adj epitax\$4 or deposit\$4) and partial near4 pressure and 117\$4.ccls.	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 14:24
-	24	sic or sic or si near2 or near10 ratio same partial near2 pressure	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 15:38
-	2	ratio same partial near2 pressure same concentrat\$4 same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 16:09
-	34	partial near2 pressure same concentrat\$4 same sic or silicon adj carbide)	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 16:01
-	79	concentrat\$4 near20 partial near2 pressure and 117/84.ccls.	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/24 17:54
-	40	concentrat\$4 near20 partial near2 pressure and 117/84-109.ccls.	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/24 17:55
-	27	flow near2 rate near10 ppm and 117/84-109.ccls.	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/24 18:20
-	132	concentrat\$4 same partial near4 pressure and 117\$4.ccls.	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 11:29
-	4	concentrat\$4 near5 chamber same partial near4 pressure and 117\$4.ccls.	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 11:31
-	90	concentrat\$4 same partial near4 pressure same proportion\$5 near5 direct\$4	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 14:59
-	61	(silicon near3 carbide or sic) near10 superlattice	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 16:35
-	34	(silicon near3 carbide or sic) near10 (CVD or chemical adj vapor near2 deposit\$4) and (time near10 thick\$4) and 117/84.ccls.	USPAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TIB	2003/05/29 16:38